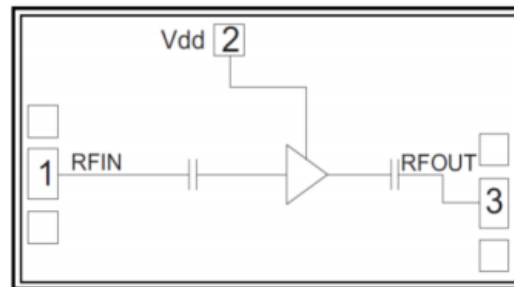


Features

- Single Biasing Voltage(Self Biased)
- Frequency: 2-6GHz
- Small Signal Gain: 26.5dB
- Noise Figure:0.9dB typ.
- P1dB: 17dBm
- Power supply: +5V/80mA
- Input/Output: 50Ω
- Die Size: 1.86 x 1.25 x 0.1 mm

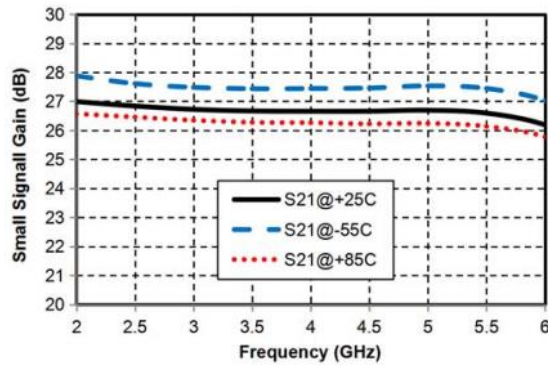
Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

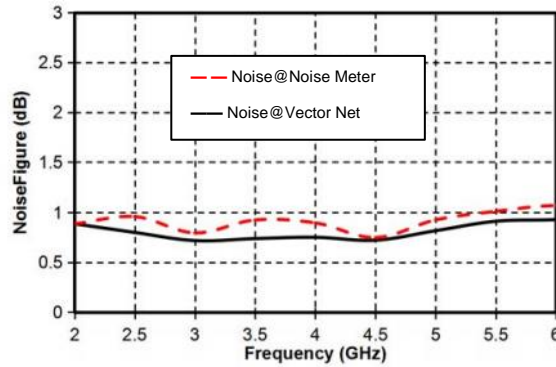
Functional Block Diagram

Electrical Specifications
TA = +25°C, Vd = +5V

Parameters	Min.	Typ.	Max.	Units
Frequency		2-6		GHz
Small Signal Gain	-	26.5	-	dB
Gain Flatness		±0.3		dB
Noise Figure (Vector Net)	-	0.9	-	dB
Noise Figure (Noise Meter)		1.0		dB
Output 1dB Compression (P1dB)	-	17	-	dBm
Psat	-	18	-	dBm
Input Return Loss	-	17	-	dB
Output Return Loss	-	22	-	dB
Static current	-	80	-	mA

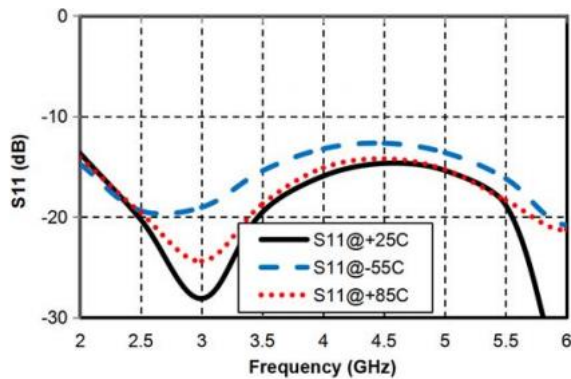
Gain vs. Frequency



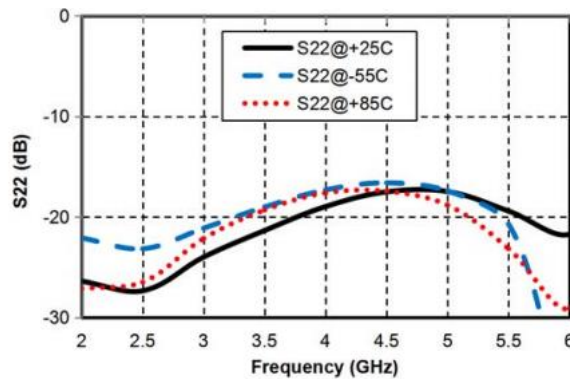
Noise Figure vs. Frequency



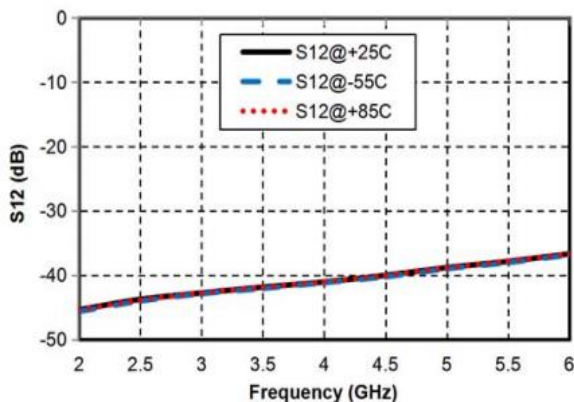
Input Return Loss vs. Frequency



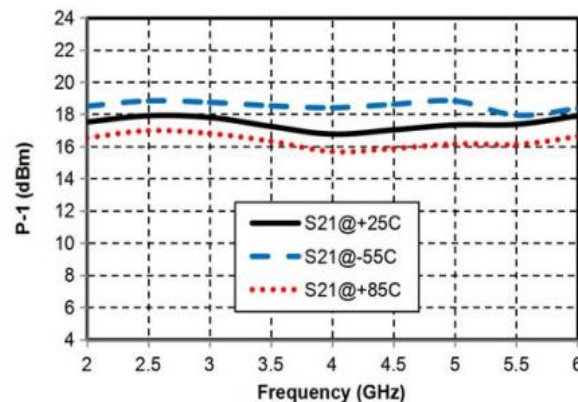
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

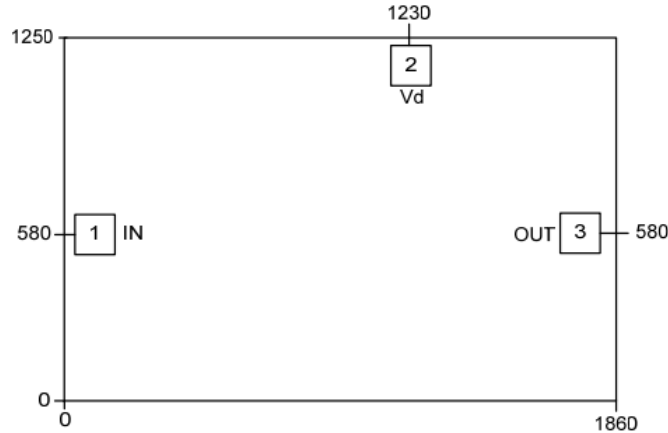


P1dB vs. Frequency





Outline Drawing: All Dimensions in μm

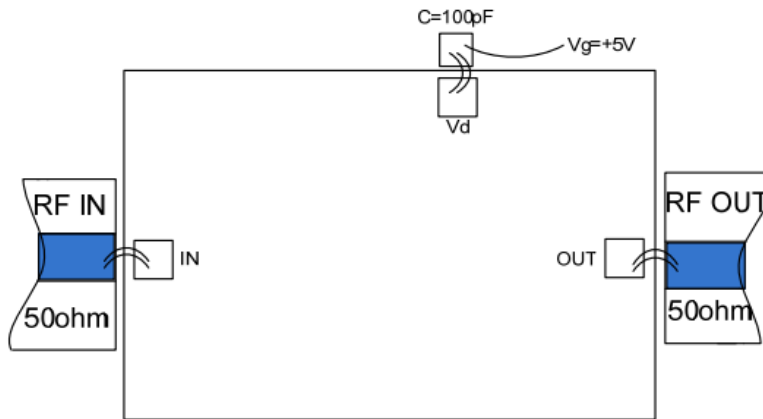


Pad Description

Pad	Function	Description
1	RF IN	RF signal input terminal, no blocking capacitor required.
3	RF OUT	RF signal output terminal, no blocking capacitor required.
2	VDD	Amplifier drain bias; external 100pF bypass capacitor required.
Die bottom	GND	Die bottom must be connected to RF/DC ground.



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C